

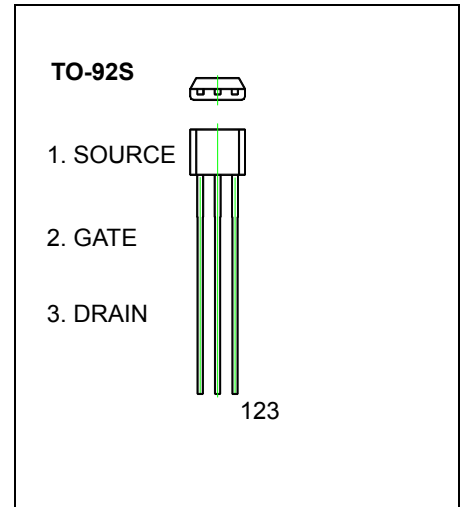


## TO-92S Plastic-Encapsulate Transistors

**K596** Si N-CHANNEL JUNCTION FET

### FEATURES

- Especially suited for use in audio, telephone capacitor microphones
- Excellent voltage characteristic
- Excellent transient characteristic



ABSOLUTE MAXIMUM RATINGS(Ta=25°C,unless otherwise specified)

PARAMETER	SYMBOL	RATING	UNIT
Gate drain voltage	$V_{GDO}$	-20	V
Gate current	$I_G$	10	mA
Drain current	$I_D$	1	mA
Power dissipation	$P_D$	100	mW
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{STG}$	-55 to+150	°C

**ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Gate-Drain breakdown Voltage	$BV_{GDO}$	$I_G = -100\mu A$	-20			V
Gate-Source cut-off Voltage	$V_{GS(off)}$	$V_{DS} = 5V, I_D = 1\mu A$		-0.6	-1.5	V
Drain Current	$I_{DSS}$	$V_{DS} = 5V, V_{GS} = 0$	100		800	$\mu A$
Forward Transfer Admittance	$ Y_{FS} $	$V_{DS} = 5V, V_{GS} = 0, f = 1KHz$	0.4	1.2		mS
Input Capacitance	$C_{iss}$	$V_{DS} = 5V, V_{GS} = 0, f = 1MHz$		3.5		pF
Output Capacitance	$C_{RSS}$	$V_{DS} = 5V, V_{GS} = 0, f = 1MHz$		0.65		pF

### $I_{DSS}$ Classification

Classification	A	B	C	D	E
$I_{DSS} (\mu A)$	100-170	150-240	210-350	320-480	440-800

